

IN THE CLAIMS:

Kindly amend claims 1-4 and add the following new claims 5-20 as shown in the following listing of claims, which replaces all previous listings and versions of claims.

1. (currently amended) A focused charged particle beam device, comprising: ~~a focused charged particle beam generating section, made up of~~ a charged particle source; ~~and~~ a focusing lens system for focusing a charged particle beam emitted from the charged particle source; ~~and~~ a blanking electrode for turning the charged particle beam ON or OFF; ~~and~~ a deflection electrode for deflecting ~~deflection scanning of the~~ focused charged particle beam to scan the charged particle beam on a sample; ~~and~~ a sample stage for supporting the sample; ~~having drive means~~ a movement mechanism for movement of the sample stage along three axes; a tilting mechanism mounted below the movement mechanism for tilting movement of the sample stage about two of the three axes, a point at which the two axes of the tilting mechanism cross being aligned with an optical axis of the focusing lens system; for adjusting beam irradiation position and angle, and a gas gun for spraying gas for deposition or to assist etching, ~~wherein the sample stage drive means comprises a mechanism capable of tilting in two axial directions, X and Y, and a mechanism capable of movement~~

~~in three dimensions, X, Y and Z, to enable tilting in all directions.~~

2. (currently amended) A ~~The focused charged particle beam device according to~~ of claim 1; wherein the focused charged particle beam is ~~, wherein a mechanism capable of movement in three dimensions X, Y and Z is mounted below a mechanism capable of tilting in two axial directions, X and Y, and a focused ion beam is adopted as the focused charged particle beam, wherein by having a mechanism capable of setting a sample surface in a tilt angle range from perpendicular to a few degrees with respect to the beam, it is made possible to carry out processing of a slice accurately and perpendicularly in all directions for a pattern of a penetrating structure of an electron beam exposure mask.~~

3. (currently amended) A ~~The focused charged particle beam device according to~~ of claim 1; further ~~, comprising means for storing data storage of a processing correction angles angle α corresponding to types of charged particle beams having different acceleration and beam current values; for a charged particle beam used, and means for controlling setting of the a sample stage to a tilt angle of $90^\circ + \alpha$ relative to the charged particle beam based on the data α , capable of carrying out perpendicular processing of a~~

~~slice in all directions for an electron beam exposure mask pattern having a penetrating structure.~~

4. (currently amended) A The focused charged particle ion beam device according to of claim 1; wherein the gas gun sprays at least one of a , provided with a function for spraying gas for assisting assist etching of a mask material and a , or deposition gas for depositing the mask material; and , from a gas gun, adopting an electron beam as the focused charged particle beam device is an electron beam.

5. (new) A focused charged particle beam device according to claim 1; wherein the tilt mechanism is a hemispherical slide mechanism comprised of a fixed body section having a hemispherical indentation; and a hemispherical protuberance angularly slidable in the hemispherical indentation.

6. (new) A focused charged particle beam device comprising: a charged particle source; a focusing lens system for focusing a charged particle beam emitted from the charged particle source; a sample stage for supporting a sample; a movement mechanism for moving the sample stage along three axes; and a tilting mechanism mounted below the movement mechanism for tilting the sample stage about two of the three axes.

7. (new) A focused charged particle beam device according to claim 6; wherein a point at which the two axes of the tilting mechanism cross is aligned with the optical axis of the focusing lens system.

8. (new) A focused charged particle beam device according to claim 6; further comprising a gas gun for spraying gas for deposition or to assist etching.

9. (new) A focused charged particle beam device according to claim 8; wherein the gas gun sprays one of a gas for assisting etching of a mask material and a deposition gas for depositing the mask material, and the focused charged particle beam is an electron beam.

10. (new) A focused charged particle beam device according to claim 6; wherein the focused charged particle beam is a focused ion beam.

11. (new) A focused charged particle beam device according to claim 1; further comprising means for storing processing correction angles α corresponding to types of charged particle beams having different acceleration or beam current values; and means for controlling setting of the sample stage to an angle of $90^\circ + \alpha$ relative to the charged particle beam based on the data α .

12. (new) A focused charged particle beam device, comprising: a charged particle source; a focusing lens system for focusing a charged particle beam emitted from the charged particle source; a sample stage for supporting a sample; and an apparatus for moving the sample stage without rotating the sample stage in a plane and comprising a movement mechanism for movement of the sample stage along three axes and a tilting mechanism for tilting movement of the sample stage about two of the three axes.

13. (new) A focused charged particle beam device according to claim 12; wherein the tilting mechanism is mounted below the movement mechanism.

14. (new) A focused charged particle beam device according to claim 13; wherein a point at which the two axes of the tilting mechanism cross is aligned with an optical axis of the focusing lens system.

15. (new) A focused charged particle beam device according to claim 12; wherein a point at which the two axes of the tilting mechanism cross is aligned with an optical axis of the focusing lens system.

16. (new) A focused charged particle beam device according to claim 12; further comprising a gas gun for spraying gas for deposition or to assist etching.

17. (new) A focused charged particle beam device according to claim 16; wherein the focused charged particle beam is an electron beam.

18. (new) A focused charged particle beam device according to claim 12; wherein the focused charged particle beam is a focused ion beam.

19. (new) A focused charged particle beam device according to claim 12; further comprising means for storing processing correction angles α corresponding to types of charged particle beams having different acceleration or beam current values; and means for controlling setting of the sample stage to an angle of $90^\circ + \alpha$ relative to the charged particle beam based on the data α .

20. (new) A focused charged particle beam device according to claim 12; wherein the tilt mechanism is a hemispherical slide mechanism comprised of a fixed body section having a hemispherical indentation; and a hemispherical protuberance angularly slidable in the hemispherical indentation.